



### 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
60V	$50m\Omega$ @ $V_{GS} = 10V$	24A
60 V	$65m\Omega @ V_{GS} = 4.5V$	21A

## Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low  $R_{DS(ON)}$  minimizes power losses
- $Low\ Q_g-minimizes\ switching\ losses$
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH6042SPDQ)

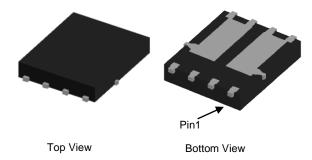
# **Description and Applications**

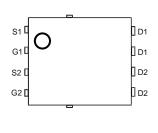
This new generation MOSFET is designed to minimize the on-state resistance R<sub>DS(ON)</sub> and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

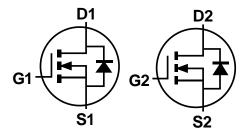
- **Engine Management Systems**
- **Body Control Electronics**
- DC-DC Converters

## **Mechanical Data**

- Case: PowerDI5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)







Pin out Top View

**Equivalent Circuit** 

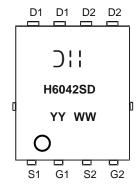
## **Ordering Information** (Note 4)

Part Number	Case	Packaging	
DMNH6042SPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free. "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



);; = Manufacturer's Marking H6042SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016)WW = Week (01 to 53)



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	60	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	5.7 4.6	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	24 17	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	32	Α		
Maximum Continuous Body Diode Forward Current (	Is	24	Α		
Avalanche Current (Note 8) L = 10mH	I <sub>AS</sub>	3.5	Α		
Avalanche Energy (Note 8) L = 10mH	Eas	65	mJ		

# 

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		$P_{D}$	1.2	W
Thermal Decistores, Junction to Ambient (Note 5)	Steady state	Б.	105	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	54	
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.5	W
Thermal Desigtance Junction to Ambient (Note 6)	Steady state	Б.	51	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	26	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	3.5	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

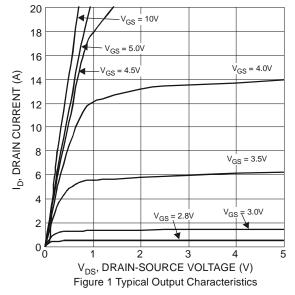
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	_	_	V	$V_{GS} = 0V$ , $I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)						_	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	45	65	11177	$V_{GS} = 4.5V, I_D = 4.4A$	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 10)						_	
Input Capacitance	Ciss	_	584	_	pF	)/ OF\/ \/ O\/	
Output Capacitance	Coss	_	83		pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	24	_	pF	1 = 1.0WHZ	
Gate Resistance	$R_g$	_	3.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	4.2		nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	8.8	_	nC	V <sub>DS</sub> = 44V. I <sub>D</sub> = 5.2A	
Gate-Source Charge	$Q_{gs}$	_	1.8	_	nC	$V_{DS} = 44V, I_{D} = 5.2A$	
Gate-Drain Charge	$Q_{gd}$	_	1.8	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.4	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 1A$	
Turn-On Rise Time	t <sub>R</sub>	_	1.9	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.1	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	4.5	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	12.9	_	ns	$I_F = 2.6A$ , $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge		_	5.4	_	nC	$I_F = 2.6A$ , $di/dt = 100A/\mu s$	

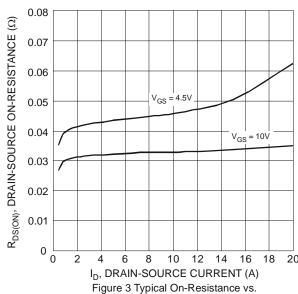
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_{J} = +25^{\circ}C$ .
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

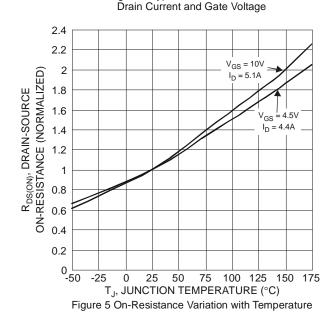
DMNH6042SPD 2 of 7 June 2016 © Diodes Incorporated Document number: DS37387 Rev. 3 - 2

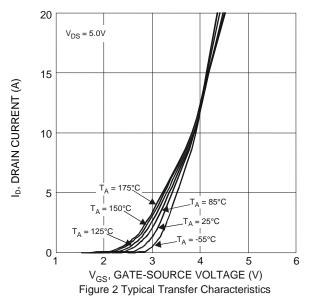


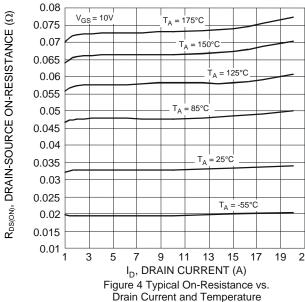


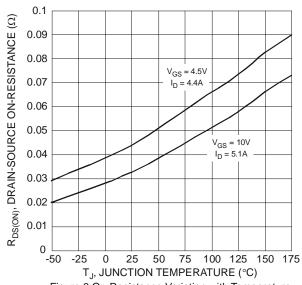














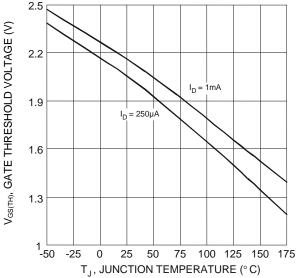


Figure 7 Gate Threshold Variation vs. Junction Temperature

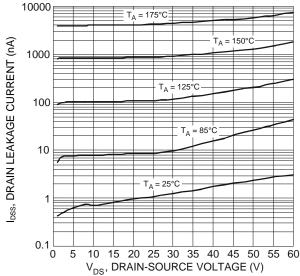
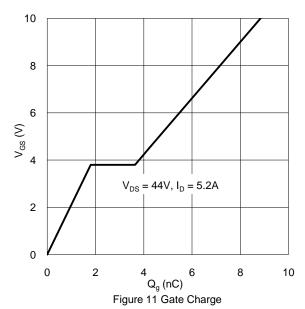
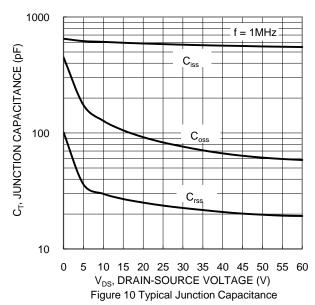


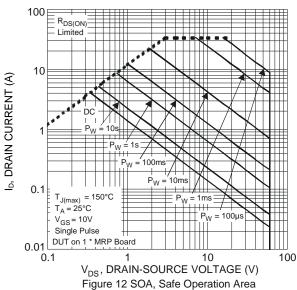
Figure 9 Typical Drain-Source Leakage Current vs. Voltage



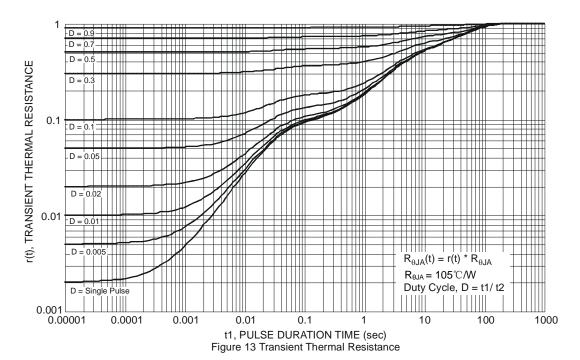
30 28 26 24 22 Is, SOURCE CURRENT (A) 20 18 16 14 12 10 T<sub>A</sub> = 150°C 8 6 T<sub>A</sub> = 85°C 4 = -55°C 2 0 0.6 0.3 0.9 1.2 1.5 V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V)

Figure 8 Diode Forward Voltage vs. Current







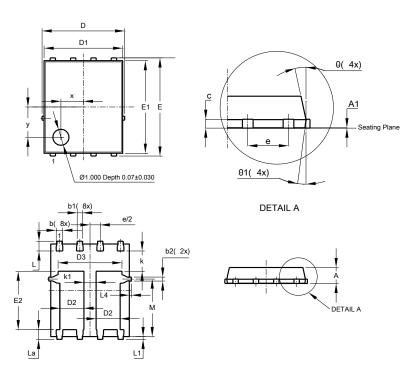




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## PowerDI5060-8 (Type C)

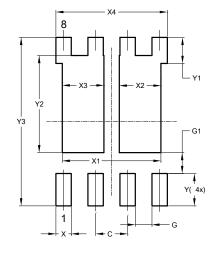


PowerDI5060-8 (Type C)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	0		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	6	.15 BS0	С		
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	1	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	1	-	0.125		
М	3.50	3.71	3.605		
х	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## PowerDI5060-8 (Type C)



Dimensions	Value			
Dillielisions	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
Χ	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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